

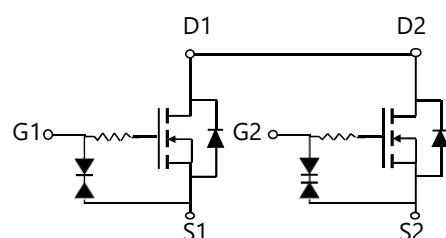
DESCRIPTION

The MX2814 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected.

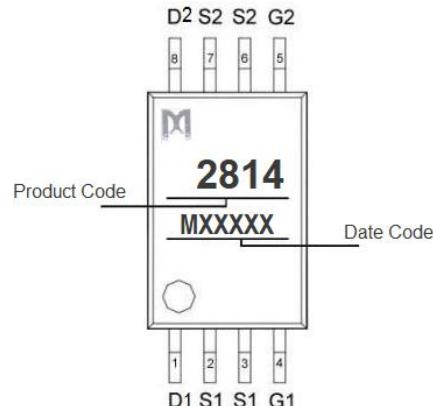
GENERAL FEATURES

- $V_{DS}=20V$, $I_D=8A$
- $R_{DS(ON)}(\text{Typ.})=11\text{m}\Omega$ @ $V_{GS}=4.5V$
- $R_{DS(ON)}(\text{Typ.})=12.5\text{m}\Omega$ @ $V_{GS}=3.8V$
- $R_{DS(ON)}(\text{Typ.})=14\text{m}\Omega$ @ $V_{GS}=2.5V$
- ESD Rating: 2000V HBM
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

PINOUT



Schematic diagram



Marking and Pin Assignment

ORDERING INFORMATION

Part Number	Marking	Storage Temperature	Package	Devices Per Reel
MX2814	MX2814	-55°C to 150°C	TSSOP-8	3000

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	8	A
Pulsed Drain Current ^(Note1)	I_{DM}	34	A
Maximum Power Dissipation	P_D	1.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

THERMAL RESISTANCE

Thermal Resistance, Junction-to-Ambient ^(Note2)	$R_{\theta JA}$	100	°C/W
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Note 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

Note 2. Surface Mounted on FR4 Board, $t \leq 10$ sec.


ELECTRICAL CHARACTERISTICS($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
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Off Characteristics

Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	± 10	μA

On Characteristics^(Note 3)

Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.45	0.7	0.95	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=2.5V, I_D=5.5A$	13	14	18	$m\Omega$
		$V_{GS}=3.8V, I_D=6A$	11	12.5	15	$m\Omega$
		$V_{GS}=4.5V, I_D=7A$	9	11	14	$m\Omega$
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=7A$	-	20	-	S

Dynamic Characteristics^(Note 4)

Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V, F=1.0MHz$	-	1150	-	pF
Output Capacitance	C_{oss}		-	185	-	pF
Reverse Transfer Capacitance	C_{rss}		-	145	-	pF

Switching Characteristics^(Note 4)

Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, R_L=1.35\Omega$ $V_{GS}=5V, R_{GEN}=3\Omega$	-	6	-	nS
Turn-on Rise Time	t_r		-	13	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	52	-	nS
Turn-Off Fall Time	t_f		-	16	-	nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=7A,$ $V_{GS}=4.5V$	-	15	-	nC
Gate-Source Charge	Q_{gs}		-	0.8	-	nC
Gate-Drain Charge	Q_{gd}		-	3.2	-	nC

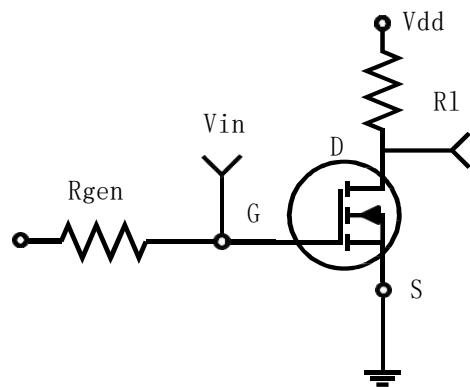
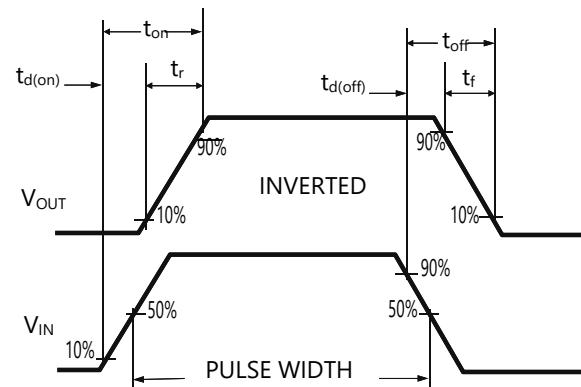
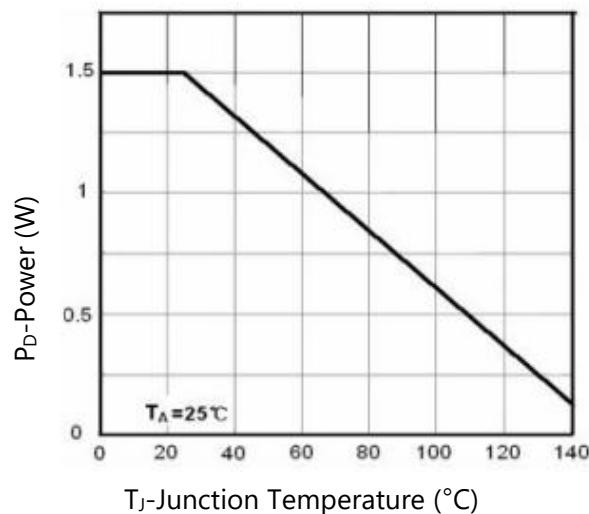
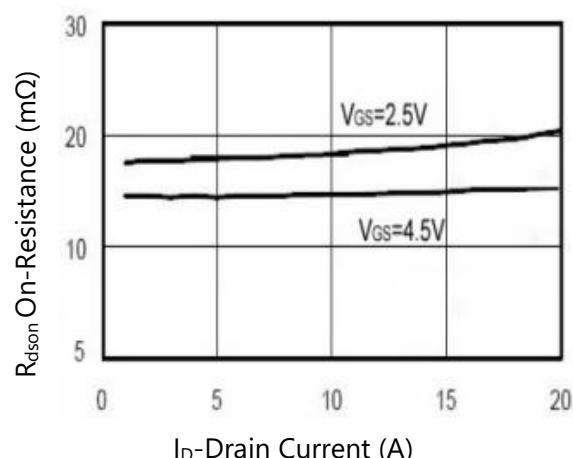
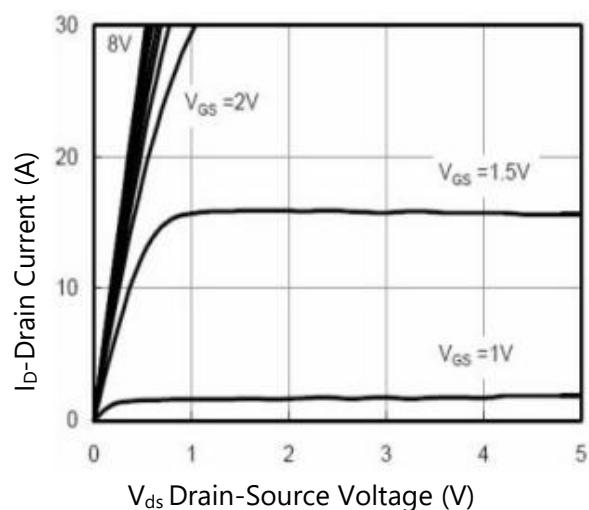
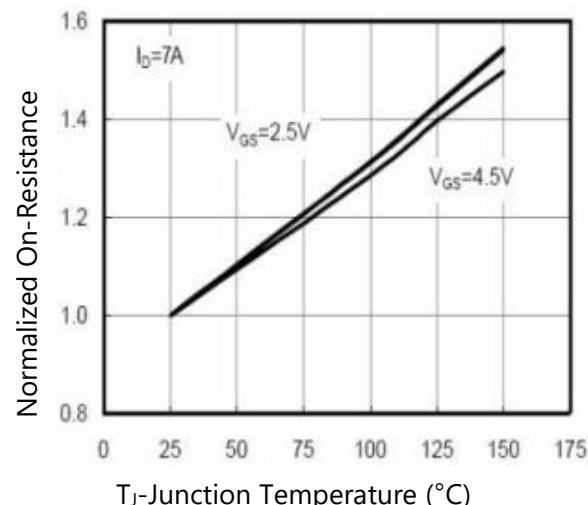
Drain-Source Diode Characteristics

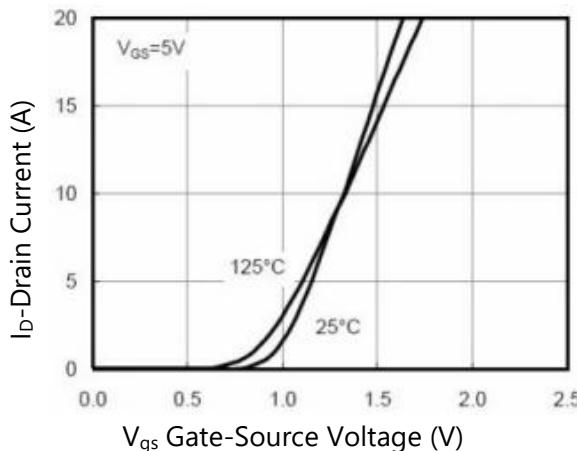
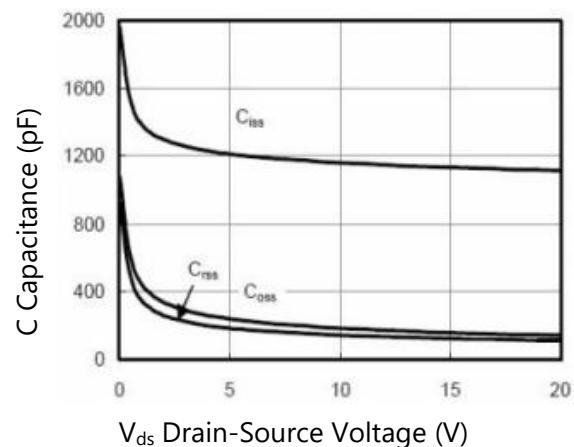
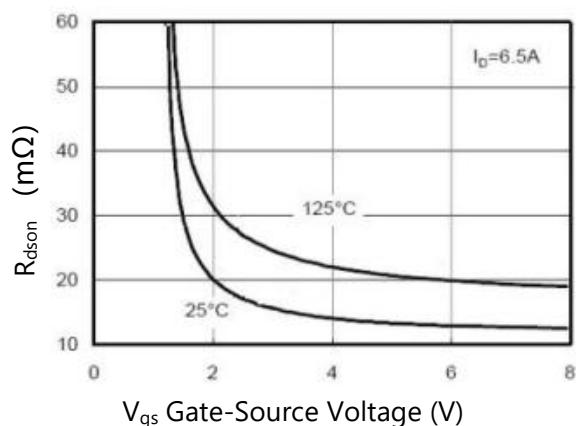
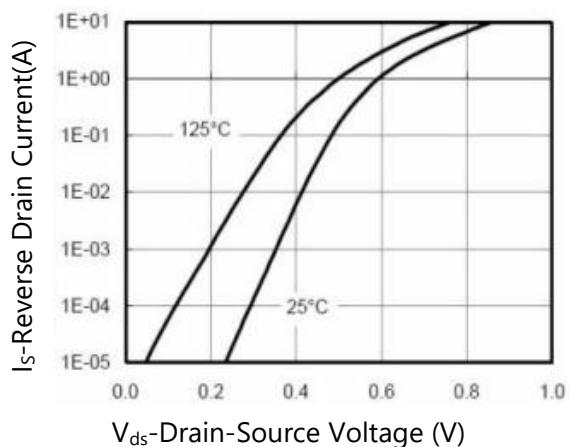
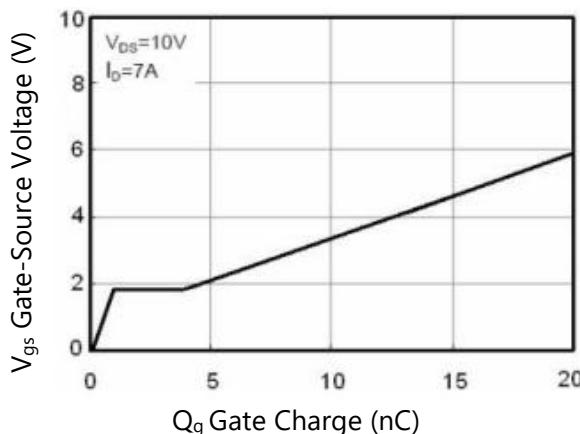
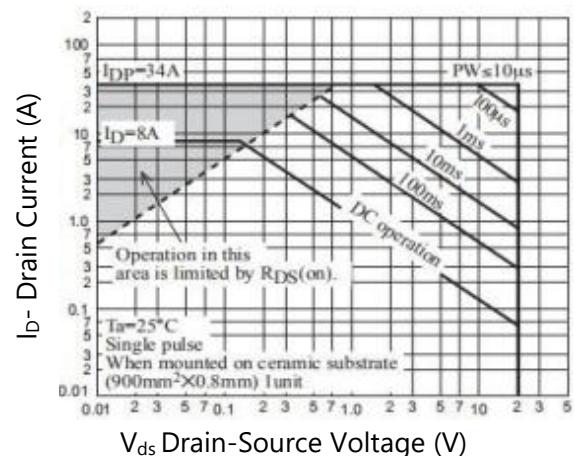
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=1A$	-	-	1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	7	A

Note 2. Surface Mounted on FR4 Board, $t \leq 10$ sec.

Note 3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

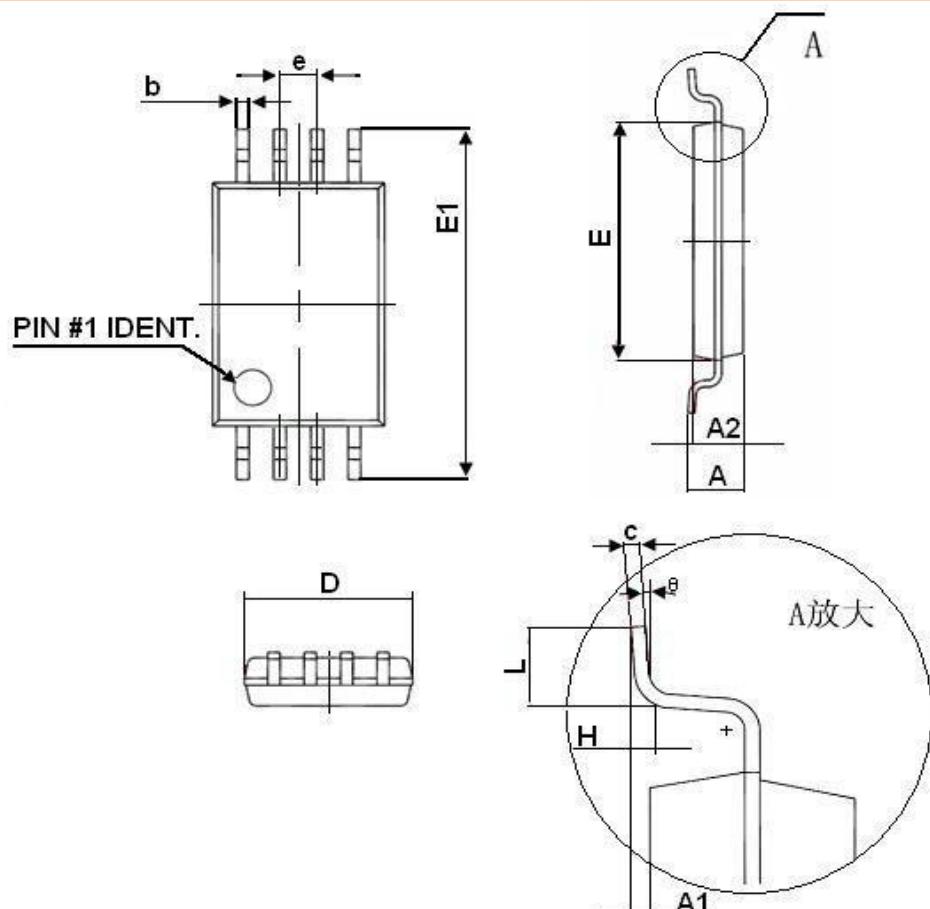
Note 4. Guaranteed by design, not subject to product.


TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 1. Switching Test Circuit

Figure 2. Switching Waveform

Figure 3. Power Dissipation

Figure 4. On-Resistance

Figure 5. Output Characteristics

Figure 6. Normalized On-Resistance



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 7. Transfer Characteristics

Figure 8. Capacitance vs V_{ds}

Figure 9. R_{dson} vs V_{gs}

Figure 10. Capacitance vs V_{ds}

Figure 11. Gate Charge

Figure 12. Safe Operation Area


PACKAGE INFORMATION

TSSOP-8



SYMBOLS	DIMENSIONS IN MILLIMETERS	
	MIN	MAX
D	2.90	3.10
E	4.30	4.50
b	0.19	0.30
c	0.09	0.20
E1	6.25	6.55
A	-	1.10
A2	0.80	1.00
A1	0.02	0.15
e	0.65(BSC)	
L	0.50	0.70
H	0.25(TYP)	
θ	1°	7°